409
withdrawn

AN   1999:56919 CAPLUS
DN   130:183514
TI   Oxetane-containing potting compositions and semiconductor devices
IN   Chiba, Hideki; Ito, Tomokazu; Shiota, Atsushi; Sato, Hozumi
PA   JSR Co., Ltd., Japan
SO   Jpn. Kokai Tokkyo Koho, 9 pp.
     CODEN: JKXXAF
DT   Patent
LA   Japanese
IC   ICM H01L023-29
     ICS H01L023-31; C08L071-02
CC   38-3 (Plastics Fabrication and Uses)
     Section cross-reference(s): 76
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI JP 11017074	A2	19990122	JP 1997-185822	19970626

AB   The compns. contain oxetane compds. Thus, a compn. contg. 99 parts XDO
     [1,4-bis[(3-ethyl-3-oxetanylmethoxy)methyl]benzene] and 1 part San-Aid SI
     100 (sulfonium-salt curing catalyst) showed gelation time 4.3, 0.5, and
     0.1 min at 75, 100, and 125.degree., resp., high fluidity, and low
     viscosity at 75.degree. and gave cured products after heating at
     125.degree. for 35 min with low linear expansion coeff.
ST   thermosetting oxetane polymer semiconductor device potting
IT   Electronic packaging materials
     Potting compositions
     Semiconductor devices
         (oxetane-contg. potting compns. and semiconductor devices)
IT   Polyoxyalkylenes, uses
     RL: DEV (Device component use); IMF (Industrial manufacture); PRP
     (Properties); TEM (Technical or engineered material use); PREP
     (Preparation); USES (Uses)
         (oxetane-contg. potting compns. and semiconductor devices)
IT   Novolaks
     RL: DEV (Device component use); IMF (Industrial manufacture); PRP
     (Properties); TEM (Technical or engineered material use); PREP
     (Preparation); USES (Uses)
         (polymers with oxetane derivs.; oxetane-contg. potting compns. and
         semiconductor devices)
IT   142627-97-2DP, polymers with phenolic novolak resin   142675-47-6P
     167488-42-8P   210093-34-8P   220527-99-1P
     RL: DEV (Device component use); IMF (Industrial manufacture); PRP
     (Properties); TEM (Technical or engineered material use); PREP
     (Preparation); USES (Uses)
         (oxetane-contg. potting compns. and semiconductor devices)

WEST

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L1: Entry 1 of 1   File: DWPI   Jan 22, 1999

DERWENT-ACC-NO: 1999-159589
DERWENT-WEEK: 199918
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TITLE: Composition for sealing semiconductor - containing oxetane compound

PATENT-ASSIGNEE:

ASSIGNEE	CODE
NIPPON GOSEI GOMU KK	JAPS

PRIORITY-DATA:
1997JP-0185822   June 26, 1997

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
JP 11017074 A	January 22, 1999	N/A	009	H01L023/29

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-NO
JP11017074A	June 26, 1997	1997JP-0185822	N/A

INT-CL (IPC): C08L 71/02; H01L 23/29; H01L 23/31

ABSTRACTED-PUB-NO: JP11017074A
BASIC-ABSTRACT:

A composition contains an oxetane compound. Also claimed is a semiconducto r is sealed by the hardened material of the composition.

USE - The compsn. is partic. used in the semiconductor device having a semiconductor integrated circuit-formed chip, a chip-mounted element substrate, an electrical connection portion formed between the substrate and an electrode terminal facing the chip, and a resin layer formed by filling voids around the electrical connection portion.

ADVANTAGE - The use of the oxetane cpd. provides the compsn. with high fluidity and quick hardening. The resulting compsn. is filled in fine voids. The use of the compsn. yields the semiconductor device suitable for high-density mounting.

CHOSEN-DRAWING: Dwg.0/2

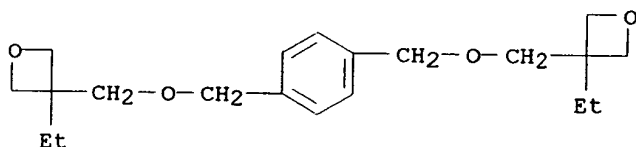TITLE-TERMS: COMPOSITION SEAL SEMICONDUCTOR CONTAIN OXETANE COMPOUND

DERWENT-CLASS: A85 E13 L03 U11

CPI-CODES: A11-B05; A12-E04; A12-E07C; E07-A03C; L04-C20A;

EPI-CODES: U11-E02A2;

CHEMICAL-CODES:

RN   **142627-97-2**   REGISTRY
CN   Oxetane, 3,3'-[1,4-phenylenebis(methyleneoxymethylene)]bis[3-ethyl- (9CI)
     (CA INDEX NAME)
OTHER NAMES:
CN   1,4-Bis[(3-ethyl-3-oxetanylmethoxy)methyl]benzene
CN   3,3'-(1,4-Xylenediylbis(oxymethylene)bis(3-ethyloxetane)
CN   3,3'-(p-Xylylene-dioxymethyl)bis(3-ethyloxetane)
FS   3D CONCORD
MF   C20 H30 O4
CI   COM
SR   CA
LC   STN Files: CA, CAPLUS, TOXLIT, USPATFULL

    19 REFERENCES IN FILE CA (1967 TO DATE)
     2 REFERENCES TO NON-SPECIFIC DERIVATIVES IN FILE CA
    20 REFERENCES IN FILE CAPLUS (1967 TO DATE)